

## REMARKS

### Election/Restriction

The election of Group I, claims 1 - 10 is affirmed.

### Title

The title has been changed.

### Drawings

The objection to the drawings under 37 CFR 1.83(a) is respectfully traversed.

Claims 3 and 5 have been cancelled, thus rendering the objection moot.

### Claim Rejections 35 USC 112

The rejection of claims 1 - 10 under 35 USC 112 is respectfully traversed.

1 Claim 1 has been amended to specify that the barrier layer is between the  
2 monocrystalline substrate and the buried strap.

3 Claim Rejections - 35 USC 102

4 The rejection of claims 1 - 7, 9 and 10 under 35 USC 102(b) is respectfully  
5 traversed.

6 Claim 1 has been amended to recite explicitly that the barrier layer is Si-C.  
7 The specification states in paragraph 23 that the term means that Si-O  
8 bonds in the silicon surface are replaced with Si - C bonds.

9 Claim 1 has been further amended, in order to distinguish clearly over the  
10 reference, to specify that the structure of the barrier layer is not that of  
11 silicon carbide.

12 In contrast, the Tsunashima reference specifies in Col. 2, lines 56 - 57 that  
13 the interface layer is silicon carbide.

14 Thus, there is a clear distinction between the invention defined by claim 1  
15 and that of the reference.

1 In addition, claim 1 further specifies that the Si-C barrier layer has been  
2 formed in the course of a plasma-assisted etch of an oxide layer. This last  
3 restriction is in the nature of a product by process limitation that has  
4 resulted in the novel structure specified earlier in the claim.


5 Claim Rejection 35 USC 103

6 The rejection of claim 8 under 35 USC 103 is respectfully traversed for the  
7 same reasons as the rejection under 35 USC 102.

8 For the foregoing reasons, allowance of the claims is respectfully  
9 solicited.

10 Respectfully submitted,  
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13 by:

  
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